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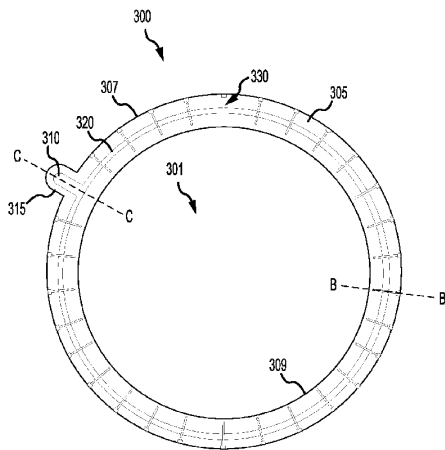


FIG. 3A

(57) Abstract: Exemplary semiconductor processing chambers may include a chamber body having sidewalls and a base. The chambers may include a pumping liner seated atop the chamber body. The pumping liner may at least partially define an annular pumping plenum and at least one exhaust aperture that fluidly couples the pumping plenum with an interior of the chamber body. The chambers may include a purge ring seated below the pumping liner. The purge ring may define an annular channel that extends about a body of the purge ring. The purge ring may define a gas inlet that is fluidly coupled with the annular channel. The purge ring may define purge ports that are disposed at different radial positions about the purge ring, each of the purge ports being aligned and in fluid communication with the pumping plenum. The chambers may include a purge gas source coupled with the gas inlet.

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